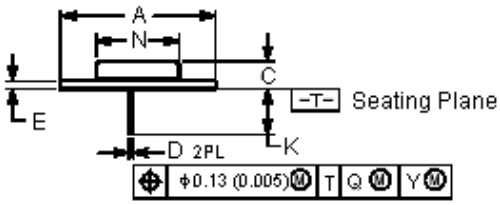
1165894

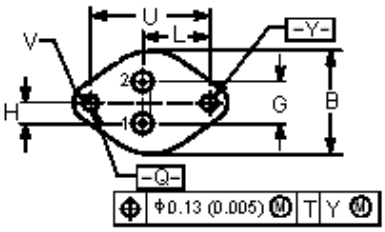
NPN silicon transistors.
Fast switching speeds and high current capacity ideally suit these parts for use in switching regulators, inverters, wide-band amplifiers and power oscillators in industrial and commercial applications.

Features:

- High speed - t_f = 0.5µs (maximum).
- High current - I_C (maximum) = 30 amperes.
- Low saturation - V_{CE} (sat) = 2.5V (maximum) at I_C = 20 amperes.
- Pb-free package.

(TO-3)



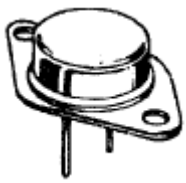


Style 1:
Pin 1. Base
2. Emitter
Collector (Case)

Dimensions	Minimum	Maximum
A	1.550 (39.37) Reference	
B	-	1.050 (26.67)
C	0.250 (6.35)	0.335 (8.51)
D	0.038 (0.97)	0.043 (1.09)
E	0.055 (1.40)	0.070 (1.77)
G	0.430 (10.92) BSC	
H	0.215 (5.46) BSC	
K	0.440 (11.18)	0.480 (12.19)
L	0.665 (16.89) BSC	
N	-	0.830 (21.08)
Q	0.151 (3.84)	0.165 (4.19)
U	1.187 (30.15) BSC	
V	0.131 (3.33)	0.188 (4.77)

Dimensions : Inches (Millimetres)

20 Ampere
NPN Silicon
Power Transistors
90 Volts - 140 Watts



(TO-3)
Case 1-07
Style 1

Maximum Ratings (Note 1)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	90	V dc
Collector-Base Voltage	V_{CBO}	150	
Collector-Emitter Voltage	V_{CEV}		
Emitter-Base Voltage	V_{EBO}	7	A dc
Collector Current-Continuous -Peak (Note 2)	I_C I_{CM}	20 30	
Base Current-Continuous	I_B	5	
Total Power Dissipation at T_C = 25°C Derate above 25°C	P_D	140 0.8	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{Stg}	-65 to +200	°C

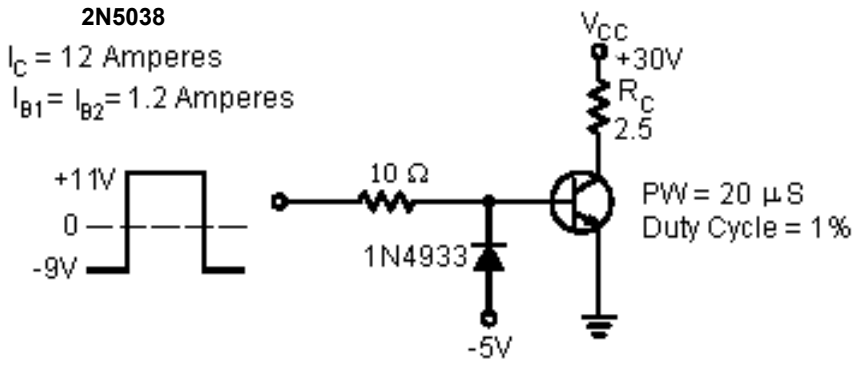
Thermal Characteristics

Characteristic	Symbol	Maximum	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.25	°C/W

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

1. Indicates JEDEC registered data.
2. Pulse test: pulse width ≤10ms, duty cycle ≤50%.

Switching Time Test Circuit

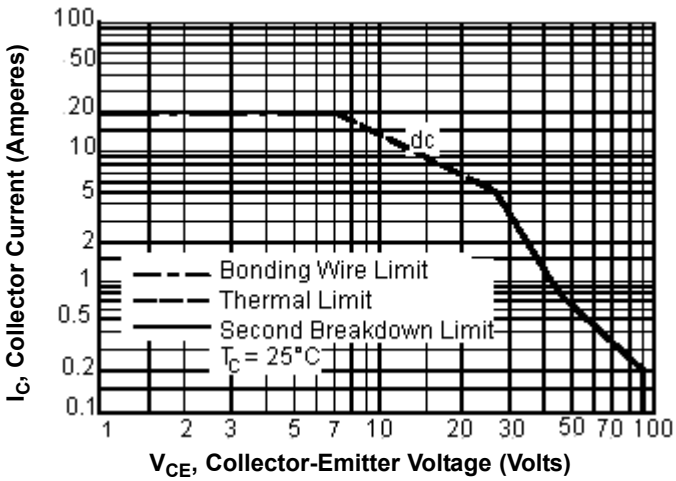


Electrical Characteristics (T_C = 25°C unless otherwise noted) (Note 3)

Characteristic		Symbol	Minimum	Maximum	Unit
Off Characteristics					
Collector-Emitter Sustaining Voltage (Note 4) (I_C = 200mA dc, I_B = 0)		$V_{CEO\ (sus)}$	90	-	V dc
Collector Cut off Current (V_{CE} = 140V dc, $V_{BE\ (off)}$ = 1.5V) (V_{CE} = 100V dc, $V_{BE\ (off)}$ = 1.5V dc, T_C = 150°C)		I_{CEX}	-	50 10	mA dc
Emitter Cut off Current (V_{EB} = 5V dc, I_C = 0) (V_{EB} = 7V dc, I_C = 0)		I_{EBO}	-	5 50	
On Characteristics (Note 4)					
DC Current Gain (I_C = 12A dc, V_{CE} = 5V dc)		h_{FE}	20	100	-
Collector-Emitter Saturation Voltage (I_C = 20A dc, I_B = 5A dc)		$V_{CE\ (sat)}$	-	2.5	V dc
Base-Emitter Saturation Voltage (I_C = 20A dc, I_B = 5A dc)		$V_{BE\ (sat)}$	-	3.3	
Dynamic Characteristics					
Magnitude of Common-Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio (I_C = 2A dc, V_{CE} = 10V dc, f = 5MHz)		$\lvert h_{fe} \rvert$	12	-	-
Switching Characteristics					
Resistive Load					
Rise Time	(V_{CC} = 30V dc) (I_C = 12A dc, I_{B1} = I_{B2} = 1.2A dc)	t_r	-	0.5	µs
Storage Time		t_s	-	1.5	

3. Indicates JEDEC Registered Data.
4. Pulse Test: Pulse Width ≤300µs, Duty Cycle ≤2%.

Forward Bias Safe Operating Area



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.
Second breakdown pulse limits are valid for duty cycles to 10%. At high case temperatures, thermal limitations may reduce the power that can be handled to values less than the limitations imposed by second breakdown.

Part Number Table

Description	Part Number
Transistor, NPN, TO-3	2N5038